

In re the Application of

Izumi FUSEGAWA et al.

Application No.: New U.S. National Stage of PCT/JP2004/011685

Filed: February 13, 2006

Docket No.: 126961

For: METHOD FOR PRODUCING A SINGLE CRYSTAL AND SILICON SINGLE CRYSTAL WAFER

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- 2. Relevance of one or more non-English language reference is discussed in the present specification. See References 5-11.
- 3. One or more reference cited herein was cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information. See References 3-5.
- 4. In accordance with 37 CFR §1.98(a)(2)(ii), copies of any U.S. patents and patent application publications are not attached.
- 5. An English language Abstract of one or more non-English language reference is attached hereto. See References 3-11.
- 6. A computer-generated English language translation of one or more Japanese Patent Publication cited herein has been obtained from the website of the Japanese Patent Office ([<http://www.jpo.go.jp>]), and is attached, but has not been reviewed for accuracy. See References 3 & 6-10.

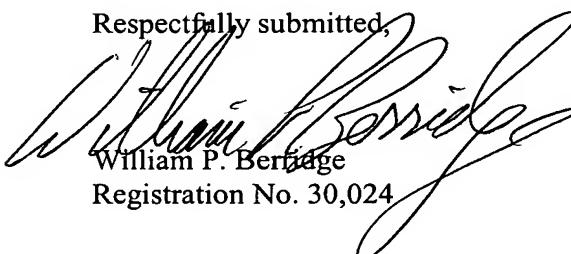
10/568186

New U.S. National Stage of PCT/JP2004/011685

IAP20 Rec'd PCT/JP 13 FEB 2006

7. Reference 1 corresponds to Reference 3. Reference 2 corresponds to Reference 4.

Respectfully submitted,


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WPB/nxy

Date: February 13, 2006

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Form PTO-1449 (REV. 1/06)			US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 126961	10/358156	APPLICATION NO. New U.S. National Stage of PCT/JP2004/011685
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)							
			APPLICANTS Izumi FUSEGAWA et al.				
			FILING DATE February 13, 2006				
U.S. PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Name			
	1.	2003/0116082 A1	06/26/2003	Masahiro SAKURADA et al.			
	2.	2002/0157600 A1	10/31/2002	Izumi FUSEGAWA et al.			
FOREIGN PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation	
	3.	JP-A-2002-201093	07/16/2002	JAPAN	X	X	
	4.	WO 01/63027 A1	08/30/2001	WIPO	X		
	5.	WO 01/81661 A1	11/01/2001	WIPO	X		
	6.	JP-A-09-202684	08/05/1997	JAPAN	X	X	
	7.	JP-A-07-041383	02/10/1995	JAPAN	X	X	
	8.	JP-A-08-330316	12/13/1996	JAPAN	X	X	
	9.	JP-A-11-147786	06/02/1999	JAPAN	X	X	
	10.	JP-A-2000-327485	11/28/2000	JAPAN	X	X	
OTHER DOCUMENTS							
Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)					
	11.	Makoto TAKIYAMA et al.; "Dielectric Degradation of Silicon Dioxide Films Cased by Metal Contaminations"; <i>Ultra Clean Technology</i> ; Vol. 5, No. 5/6; Nippon Steel Corporation; pp. 345-359. (with abstract)					
EXAMINER						DATE CONSIDERED	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							